
2SC3553

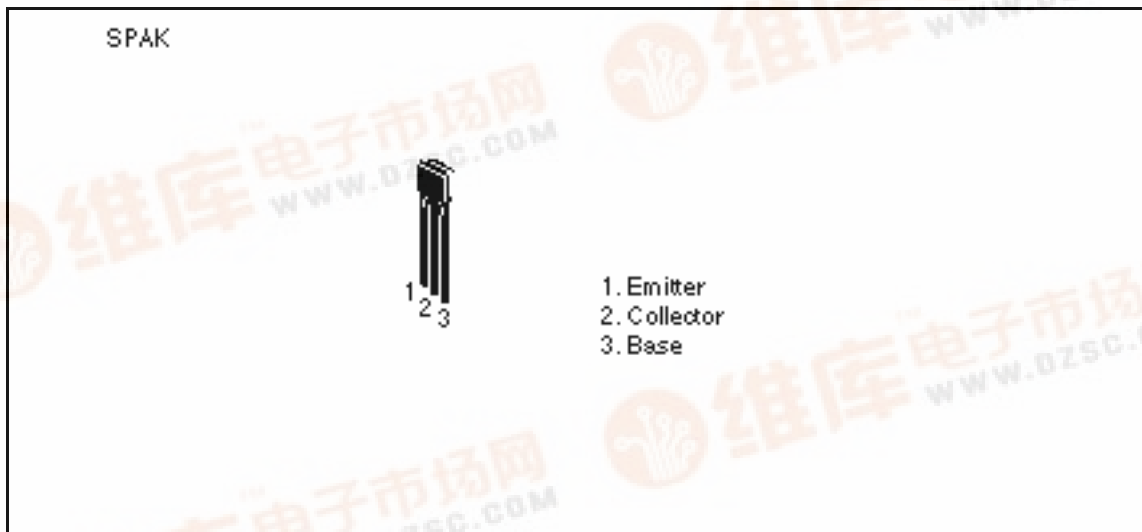
Silicon NPN Epitaxial

HITACHI

Application

Low frequency amplifier

Outline



2SC3553

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	35	V
Collector to emitter voltage	V_{CEO}	35	V
Emitter to base voltage	V_{EBO}	4	V
Collector current	I_C	500	mA
Collector power dissipation	P_C	300	mW
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55 to +150	°C

Electrical Characteristics (Ta = 25°C)

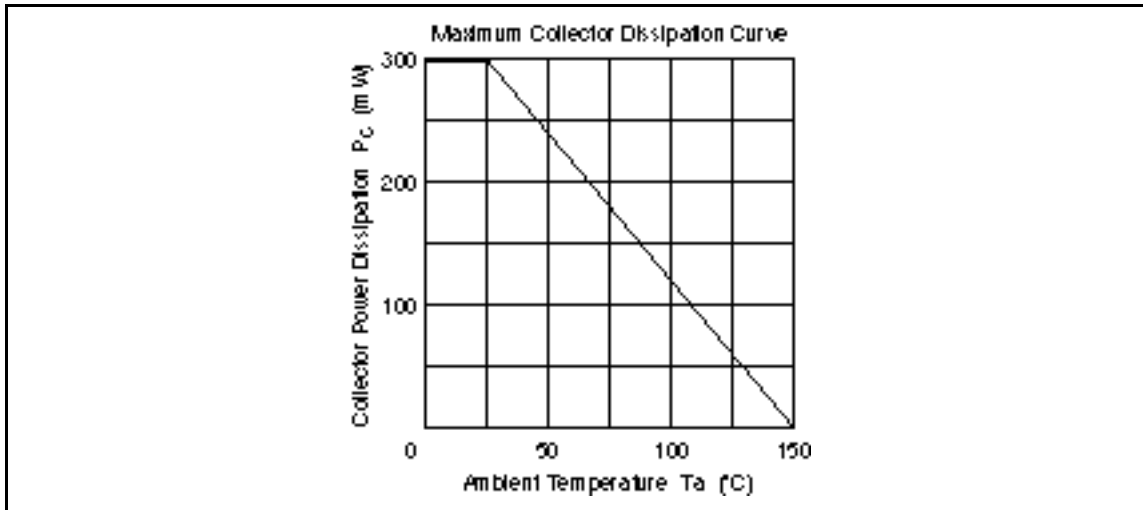
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	35	—	—	V	$I_C = 10 \mu A, I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	35	—	—	V	$I_C = 1 \text{ mA}, R_{BE} =$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	4	—	—	V	$I_E = 10 \mu A, I_C = 0$
Collector cutoff current	I_{CBO}	—	—	0.5	μA	$V_{CB} = 20 \text{ V}, I_E = 0$
DC current transfer ratio	h_{FE1}^{*1}	60	—	320		$V_{CE} = 3 \text{ V}, I_C = 10 \text{ mA}$
	h_{FE2}	10	—	—		$V_{CE} = 3 \text{ V}, I_C = 500 \text{ mA}^{*2}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	0.2	0.6	V	$I_C = 150 \text{ mA}, I_B = 15 \text{ mA}^{*2}$
Base to emitter voltage	V_{BE}	—	0.64	—	V	$V_{CE} = 3 \text{ V}, I_C = 10 \text{ mA}$

Notes: 1. The 2SC3553 is grouped by h_{FE1} as follows.

2. Pulse test

B	C	D
60 to 120	100 to 200	160 to 320

See characteristic curves of 2SC1213.



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HITACHI

Hitachi, Ltd.

Semiconductor & IC Div.
Nippon Bldg., 2-6-2, Ohite-machi, Chiyoda-ku, Tokyo 100, Japan
Tel: Tokyo (03) 3270-2111
Fax: (03) 3270-5109

For further information write to:

Hitachi America, Ltd.
Semiconductor & IC Div.
2000 Sierra Point Parkway
Brisbane, CA. 94005-4835
U.S.A.
Tel: 415-589-8300
Fax: 415-589-4207

Hitachi Europe GmbH
Electronic Components Group
Continental Europe
Dornacher StraÙe 3
D-85622 Feldkirchen
München
Tel: 089-9 94 80 0
Fax: 089-9 29 30 00

Hitachi Europe Ltd.
Electronic Components Div.
Northern Europe Headquarters
Whitbrook Park
Lower Cookham Road
M Maidenhead
Berkshire SL6 8YA
United Kingdom
Tel: 0628-585000
Fax: 0628-778322

Hitachi Asia Pte. Ltd.
45 Collyer Quay #20-00
Hitachi Tower
Singapore 0404
Tel: 535-2100
Fax: 535-1533

Hitachi Asia (Hong Kong) Ltd.
Unit 705, North Tower,
World Finance Centre
Harbour City, Canton Road
Tsim Sha Tsui, Kowloon
Hong Kong
Tel: 27359218
Fax: 27308074